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General Description:

A gallium arsenide infrared-emitting diode and a npn-silicon-darlington-connected phototransistor on a 6 lead frame encapsulated; 0.350 in. Lg; 0.200 in. Maximum h; 0.300 in. W; plastic dual-in-line case; input to output voltage porm 1.5 kv; 7 v emitter-collector voltage; input diode reverse voltage 3 v; 250.0 mw; 0.52 grams wt

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fig:

A23900